

N-Channel MOSFET

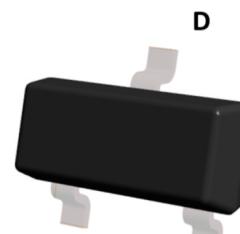
Description

- Trench Power LV MOSFET technology
- High Power and current handing capability

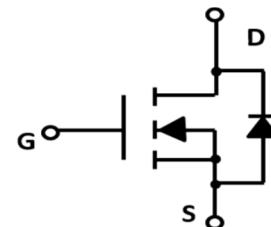
| MOSFET Product Summary | | |
|------------------------|---------------------------|--------------------|
| V _{DS} (V) | R _{DS(on)} (mΩ) | I _D (A) |
| 20 | 30@V _{GS} = 4.5V | 4.0 |
| | 45@V _{GS} = 2.5V | |

Applications

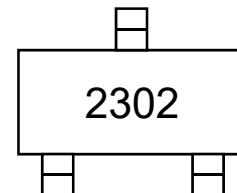
- PWM application
- Load switch



Top View



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

| Rating | Symbol | Value | Units |
|---|-----------------------------------|----------|-------|
| Drain-source Voltage | V _{DS} | 20 | V |
| Gate-source Voltage | V _{GS} | ±10 | V |
| Drain Current | I _D | 4.0 | A |
| | | 3.5 | |
| Pulsed Drain Current ¹⁾ | I _{DM} | 18 | A |
| Total Power Dissipation @ T _A =25°C | P _D | 1.0 | W |
| Thermal Resistance Junction-to-Ambient @ Steady State ²⁾ | R _{θJA} | 125 | °C/W |
| Junction and Storage Temperature Range | T _J , T _{STG} | -55~+150 | °C |

Notes:

1) Pulse Test: Pulse Width≤300μs,Duty cycle ≤2%.

2) Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Units |
|---------------------------------------|--------------|---|------|------|-----------|-----------|
| Static Parameter | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 20 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 16V, V_{GS} = 0V, T_C = 25^\circ C$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS} = \pm 10V, V_{DS} = 0V$ | - | - | ± 100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.5 | 0.7 | 1.0 | V |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS} = 4.5V, I_D = 4.0A$ | - | - | 30 | $m\Omega$ |
| | | $V_{GS} = 2.5V, I_D = 3.0A$ | - | - | 45 | |
| Diode Forward Voltage | V_{SD} | $I_S = 4.3A, V_{GS} = 0V$ | - | - | 1.2 | V |
| Maximum Body-Diode Continuous Current | I_S | | - | - | 4.0 | A |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$ | - | 595 | - | pF |
| Output Capacitance | C_{oss} | | - | 106 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 59 | - | |
| Switching Parameters | | | | | | |
| Total Gate Charge | Q_g | $V_{GS} = 4.5V, V_{DS} = 10V, I_D = 4.0A$ | - | 6.6 | - | nC |
| Gate Source Charge | Q_{gs} | | - | 0.9 | - | |
| Gate Drain Charge | Q_{gd} | | - | 1.4 | - | |
| Turn-on Delay Time | $t_{D(on)}$ | $V_{GS} = 4.5V, V_{DD} = 10V, R_L = 1.5\Omega, R_{GEN} = 3\Omega$ | - | 13 | - | ns |
| Turn-on Rise Time | t_r | | - | 54 | - | |
| Turn-off Delay Time | $t_{D(off)}$ | | - | 18 | - | |
| Turn-off Fall Time | t_f | | - | 11 | - | |

Typical Characteristics

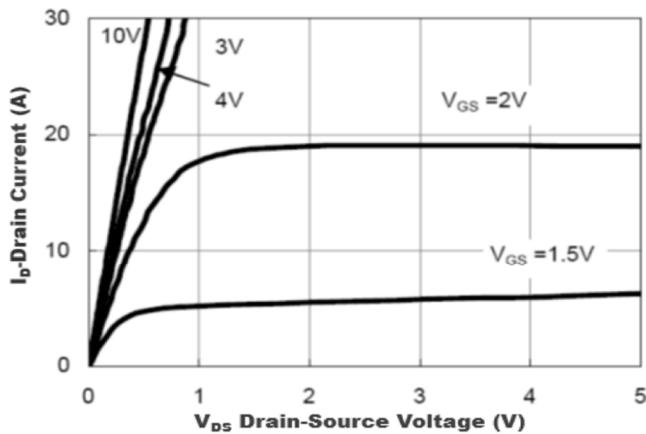


Figure1. Output Characteristics

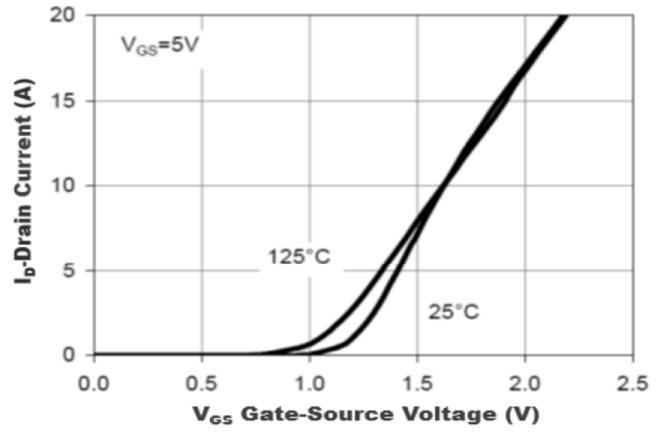


Figure2. Transfer Characteristics

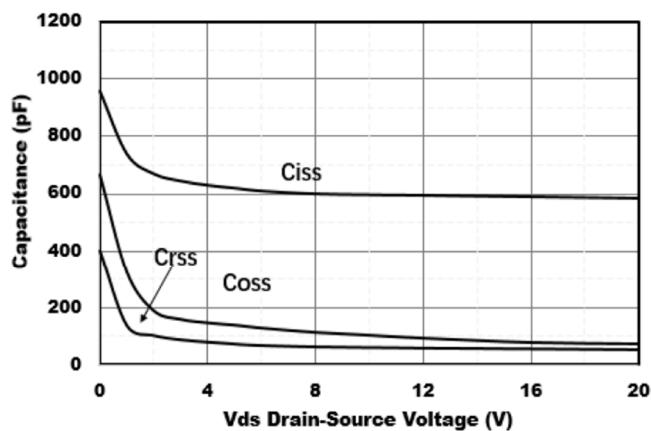


Figure3. Capacitance Characteristics

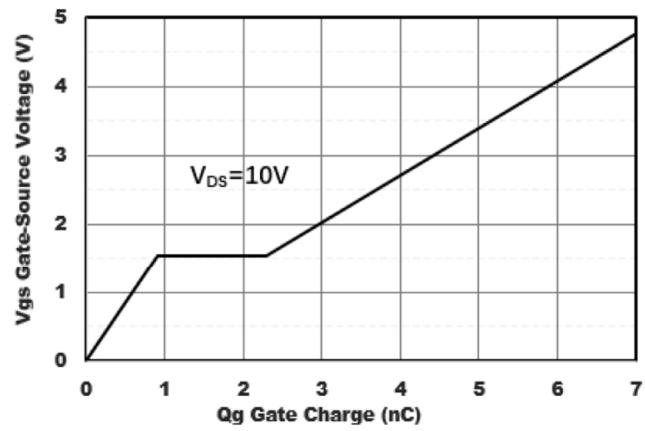


Figure4. Gate Charge

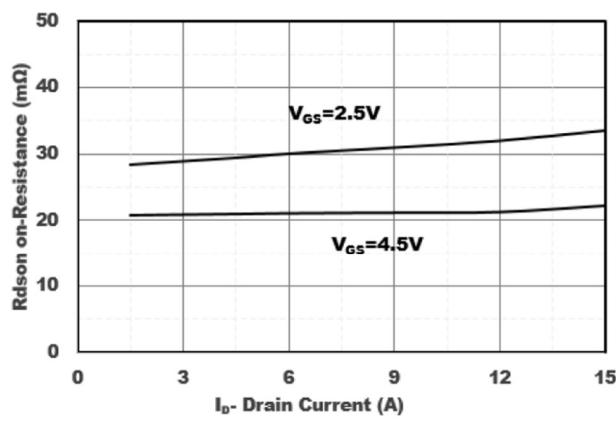


Figure5. Drain-Source on Resistance

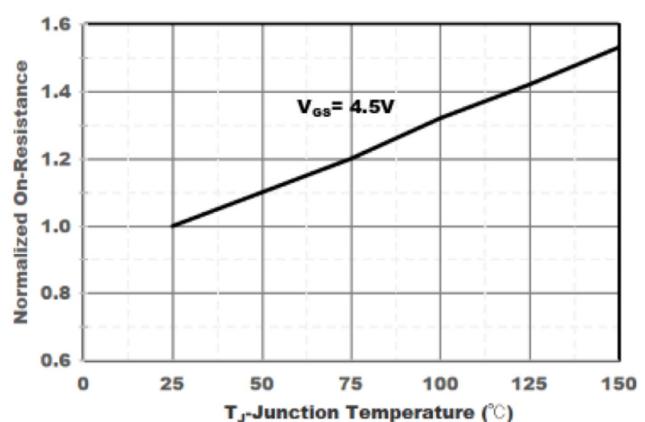


Figure6. Drain-Source on Resistance

N-Channel MOSFET

PNMT2302

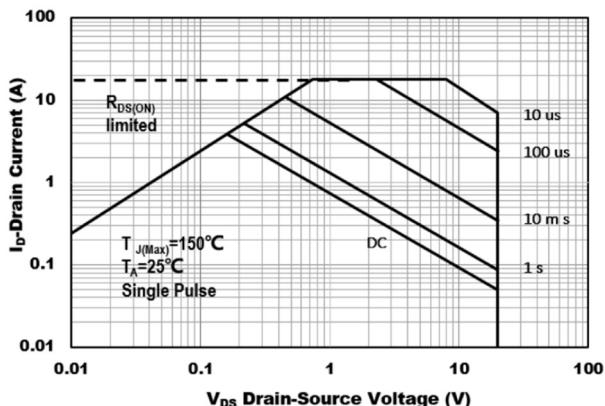


Figure 7. Safe Operation Area

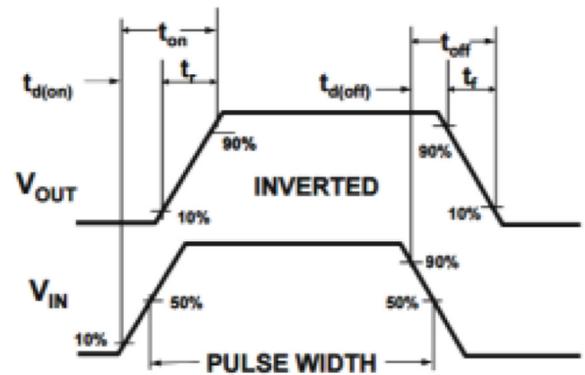
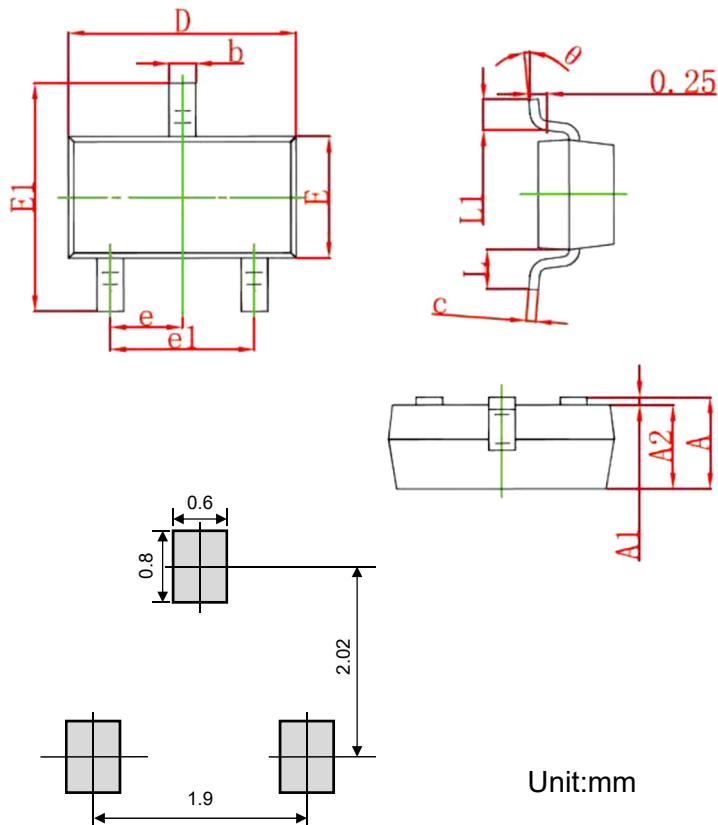


Figure 8. Switching wave

Product dimension (SOT-23)



Suggested PCB Layout

| Dim | Millimeters | | Inches | |
|-----|-------------|-------|------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 Typ. | | 0.037 Typ. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 Ref. | | 0.022 Ref. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

Ordering information

| Device | Package | Reel | Shipping |
|----------|------------------|------|--------------------|
| PNMT2302 | SOT-23 (Pb-Free) | 7" | 3000 / Tape & Reel |

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